## 1. General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 2. Features and benefits

- · Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

# 3. Applications

- DC-to-DC converters
- Switched-mode power supplies

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit			
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	200	V			
I <sub>D</sub>	drain current	T <sub>mb</sub> = 100 °C		-	-	27.5	Α			
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C		-	-	250	W			
Static characte	Static characteristics									
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 17 \text{ A}; T_j = 175 ^{\circ}\text{C}$		-	-	165	mΩ			
Dynamic characteristics										
$Q_{GD}$	gate-drain charge	$I_D = 39 \text{ A}; V_{DS} = 160 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}$		-	37	50	nC			



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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	
2	D	drain		
3	S	source		D
mb	D	mounting base; connected to drain		G mbb076 S
			TO-220AB (SOT78)	

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package		
	Name	Description	Version
PSMN057-200P		plastic, single-ended package (heatsink mounted, 1 mounting hole); 3 leads; 2.54 mm pitch; 15.6 mm x 10 mm x 4.4 mm body	SOT78

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN057-200P	PSMN057 200P

# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	200	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ Tj ≤ 175 °C; RGS = 20 kΩ	-	200	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	250	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 100 °C	-	27.5	A
		T <sub>mb</sub> = 25 °C	-	39	A
I <sub>DM</sub>	peak drain current	pulsed; T <sub>mb</sub> = 25 °C	-	156	A
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
Source-drain di	ode				
Is	source current	T <sub>mb</sub> = 25 °C	-	39	А

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Symbol	Parameter	Conditions		Min	Max	Unit		
I <sub>SM</sub>	peak source current	pulsed; T <sub>mb</sub> = 25 °C		-	156	Α		
Avalanche r	Avalanche ruggedness							
E <sub>DS(AL)S</sub>	source avalanche energy	$I_D$ = 23 A; $V_{sup} \le 50$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p$ = 240 μs		-	925	mJ		
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} \le 50 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega; \text{ unclamped}$		-	23	А		

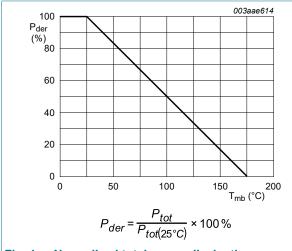


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

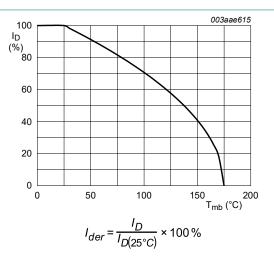


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

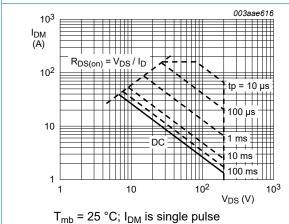
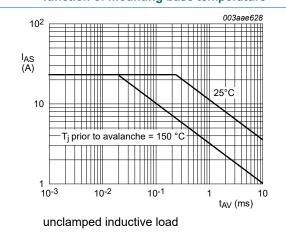


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



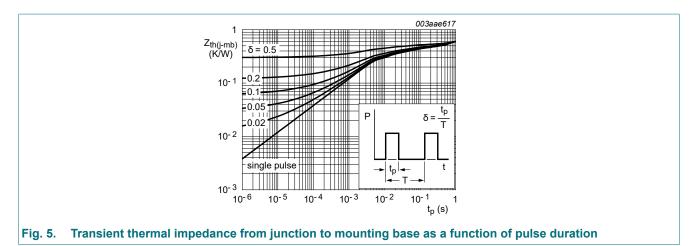
 ig. 4. Single-shot avalanche rating; avalanche current as a function of avalanche period

### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base		-	-	0.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

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### 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$	178	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	200	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C	-	-	6	V
	voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C	1	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	2	3	4	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 200 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.03	10	μA
		V <sub>DS</sub> = 200 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 17 A; T <sub>j</sub> = 175 °C	-	-	165	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 17 A; T <sub>j</sub> = 25 °C	-	41	57	mΩ
Dynamic ch	naracteristics		<b>'</b>	<b>'</b>		
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 39 A; V <sub>DS</sub> = 160 V; V <sub>GS</sub> = 10 V;	-	96	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	13	-	nC
Q <sub>GD</sub>	gate-drain charge	7	-	37	50	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	3750	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	385	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	180	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 100 \text{ V}; R_L = 2.7 \Omega; V_{GS} = 10 \text{ V};$	-	18	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 °C$	-	58	-	ns
t <sub>d(off)</sub>	turn-off delay time	7	-	105	-	ns
t <sub>f</sub>	fall time	1	-	78	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain lead to centre of die; T <sub>j</sub> = 25 °C	-	4.5	-	nΗ
		measured from tab to centre of die; $T_j = 25  ^{\circ}\text{C}$	-	3.5	-	nH
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad; T <sub>i</sub> = 25 °C	-	7.5	-	nΗ

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Source-drain diode								
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	0.85	1.2	V	
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;		-	133	-	ns	
Q <sub>r</sub>	recovered charge	$V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$		-	895	-	nC	

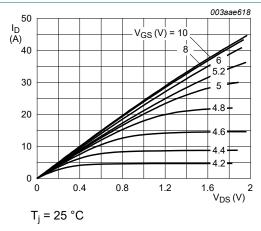


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

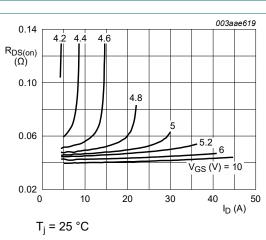


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values

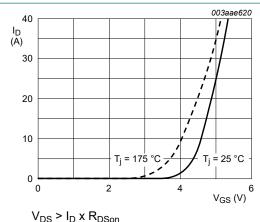


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

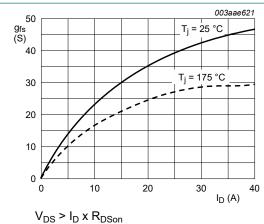


Fig. 9. Forward transconductance as a function of drain current; typical values

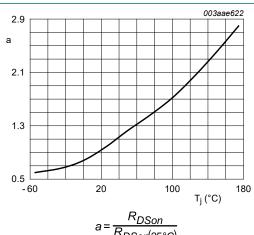
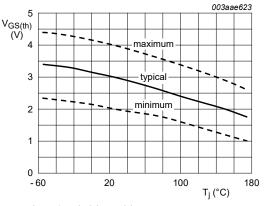


Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature



 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}$ 

Fig. 11. Gate-source threshold voltage as a function of junction temperature

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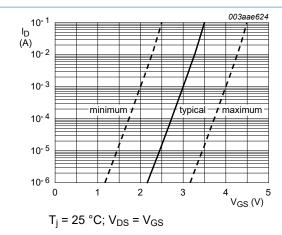
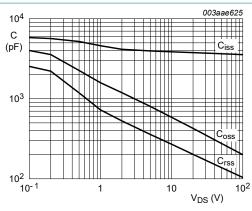


Fig. 12. Sub-threshold drain current as a function of gate-source voltage



 $V_{GS} = 0 V; f = 1 MHz$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

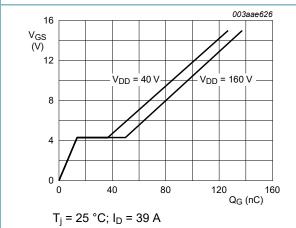


Fig. 14. Gate-source voltage as a function of gate charge; typical values

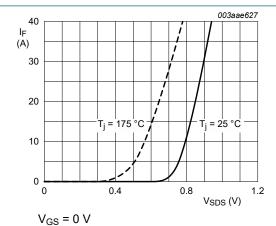
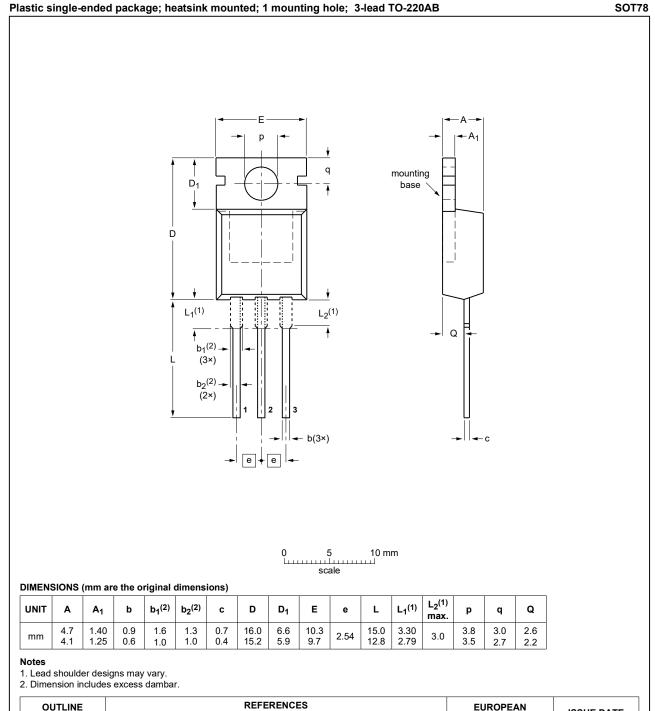


Fig. 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical

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# 11. Package outline



OUTLINE	REFERENCES			REFERENCES EUROP		ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

Fig. 16. Package outline TO-220AB (SOT78)

#### N-channel TrenchMOS SiliconMAX standard level FET

### 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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